

Title (en)
Testing circuit for random access memory device.

Title (de)
Prüfschaltung für eine Speichereinrichtung mit willkürlichen Zugriff.

Title (fr)
Circuit d'essai pour des dispositifs de mémoire à accès direct.

Publication
EP 0253161 A1 19880120 (EN)

Application
EP 87109030 A 19870624

Priority
JP 15034786 A 19860625

Abstract (en)
In a semiconductor random access memory device of the type having two or more data lines arranged in association with a single data input or output terminal is provided a memory testing circuit which is characterized in that test data is supplied to every one of the data lines and is written all at a time into a plurality of memory cells which may include those located adjacent each other, wherein the number of the memory cells into which test data is to be written simultaneously depends on the data lines to be selected so that different pieces of data can be respectively written into the individual memory cells. A portion of an address signal is used not for the selection of the memory cells during the test data write cycle of the testing operation but for controlling the inversion of the test data to be written into selected ones of the memory cells and is supplied to the memory cells associated with any one or more of the data lines, whereby pieces of data complementary to each other can be supplied to the adjacent memory cells respectively through two of the data lines, providing a basis on which an interference test can be conducted for the memory cells located adjacent each other.

IPC 1-7
G11C 29/00; G11C 11/00; G01R 31/28; H01L 21/66

IPC 8 full level
G11C 29/00 (2006.01); **G11C 11/401** (2006.01); **G11C 11/409** (2006.01); **G11C 29/34** (2006.01)

CPC (source: EP US)
G11C 29/34 (2013.01 - EP US)

Citation (search report)
• DE 2641727 A1 19770317 - ERICSSON TELEFON AB L M
• DE 1554502 B
• EP 0055918 A2 19820714 - FUJITSU LTD [JP]
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• EP 0055129 A2 19820630 - FUJITSU LTD [JP]
• DE 2846890 A1 19800508 - SIEMENS AG

Cited by
GB2235555A; GB2235555B; EP0886280A1; DE4243611A1; DE4243611B4; GB2232496A; GB2232496B

Designated contracting state (EPC)
DE FR GB

DOCDB simple family (publication)
EP 0253161 A1 19880120; EP 0253161 B1 19911016; DE 3773773 D1 19911121; JP S63106998 A 19880512; US 4888772 A 19891219

DOCDB simple family (application)
EP 87109030 A 19870624; DE 3773773 T 19870624; JP 15924987 A 19870625; US 6627587 A 19870625